BC640, BC640-16

High Current Transistors

Symbol

 V_{CEO}

V_{CBO}

VFBO

 I_{C}

 P_D

 P_D

T_J, T_{stg}

Symbol

 $R_{\theta JA}$

 $R_{\theta JC}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the

Recommended Operating Conditions may affect device reliability.

PNP Silicon

MAXIMUM RATINGS

Collector-Emitter Voltage

Collector-Base Voltage

Collector Current - Continuous

Operating and Storage Junction

THERMAL CHARACTERISTICS

Characteristic

Thermal Resistance, Junction-to-Ambient

Thermal Resistance, Junction-to-Case

Total Device Dissipation @ $T_A = 25^{\circ}C$

Total Device Dissipation @ T_C = 25°C

Emitter-Base Voltage

Derate above 25°C

Derate above 25°C

Temperature Range

Features

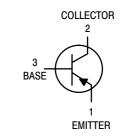
• Pb-Free Packages are Available*

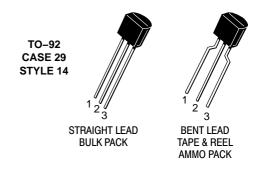
Rating



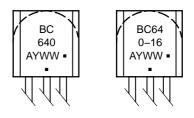
ON Semiconductor®

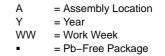
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MARKING DIAGRAMS





(Note: Microdot may be in either location)

ORDERING INFORMATION See detailed ordering and shipping information in the package

dimensions section on page 2 of this data sheet.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

Unit

Vdc

Vdc

Vdc

Adc

mW

mW/°C

W

mW/°C

°C

Unit

°C/W

°C/W

Value

-80

-80

-5.0

-0.5

625

5.0

1.5

12

-55 to +150

Max

200

83.3

BC640, BC640-16

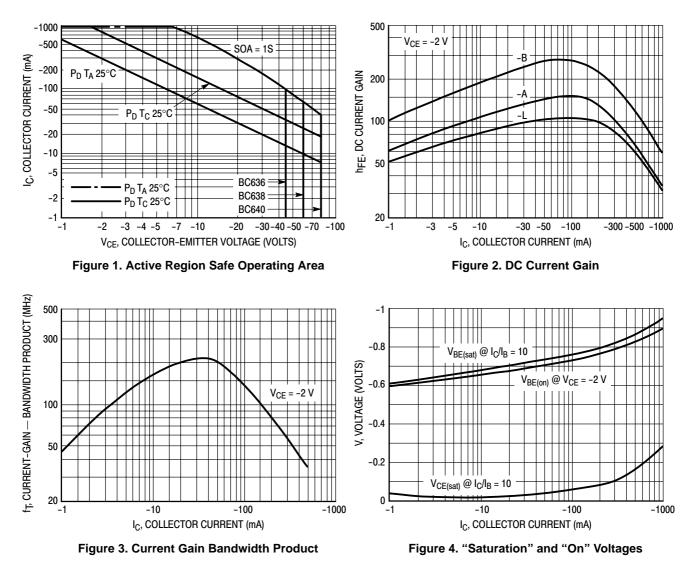
ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Collector – Emitter Breakdown Voltage ($I_C = -10 \text{ mAdc}, I_B = 0$)	V _{(BR)CEO}	-80	_	_	Vdc
Collector – Base Breakdown Voltage $(I_C = -100 \ \mu Adc, I_E = 0)$	V _{(BR)CBO}	-80	_	_	Vdc
Emitter – Base Breakdown Voltage $(I_E = -10 \ \mu Adc, I_C = 0)$	V _{(BR)EBO}	-5.0	-	_	Vdc
Collector Cutoff Current $(V_{CB} = -30 \text{ Vdc}, I_E = 0)$ $(V_{CB} = -30 \text{ Vdc}, I_E = 0, T_A = 125^{\circ}\text{C})$	I _{СВО}			-100 -10	nAdc μAdc
ON CHARACTERISTICS (Note 1)					
$ \begin{array}{l} \mbox{DC Current Gain} \\ (I_C = -5.0 \mbox{ mAdc}, V_{CE} = -2.0 \mbox{ Vdc}) \\ (I_C = -150 \mbox{ mAdc}, V_{CE} = -2.0 \mbox{ Vdc}) \\ (I_C = -500 \mbox{ mA}, V_{CE} = -2.0 \mbox{ V}) \end{array} \end{array} \\ \begin{array}{l} \mbox{BC640} \\ \mbox{BC640} - 16 \end{array} $	h _{FE}	25 40 100 25	- - -	_ 160 250 _	_
Collector – Emitter Saturation Voltage ($I_C = -500 \text{ mAdc}$, $I_B = -50 \text{ mAdc}$)	V _{CE(sat)}		-0.25 -0.5	-0.5 -	Vdc
Base – Emitter On Voltage ($I_C = -500 \text{ mAdc}, V_{CE} = -2.0 \text{ Vdc}$)	V _{BE(on)}	_	_	-1.0	Vdc
DYNAMIC CHARACTERISTICS					
Current Gain – Bandwidth Product ($I_C = -50$ mAdc, $V_{CE} = -2.0$ Vdc, f = 100 MHz)	f _T	-	150	_	MHz
Output Capacitance $(V_{CB} = -10 \text{ Vdc}, I_E = 0, f = 1.0 \text{ MHz})$	C _{ob}	_	9.0	_	pF
Input Capacitance $(V_{EB} = -0.5 \text{ Vdc}, I_C = 0, f = 1.0 \text{ MHz})$	C _{ib}	-	110	_	pF

1. Pulse Test: Pulse Width \leq 300 µs, Duty Cycle 2.0%.

ORDERING INFORMATION

Device	Package	Shipping	
BC640G	TO–92 (Pb–Free)	5000 Units / Bulk	
BC640ZL1G	TO–92 (Pb–Free)	2000 Units / Ammo Box	
BC640–16	TO-92	5000 Units / Bulk	
BC640–16G	TO-92 (Pb-Free)	5000 Units / Bulk	



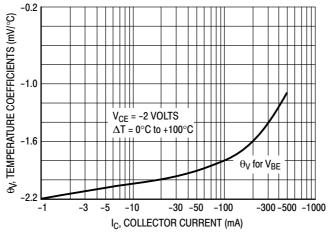
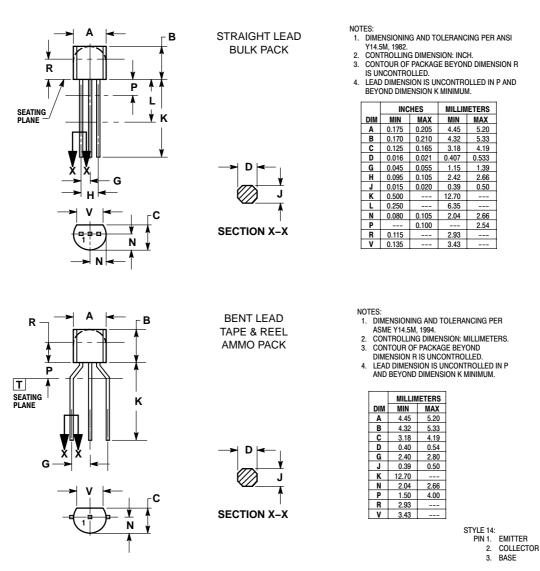


Figure 5. Temperature Coefficients

PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 ISSUE AM



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